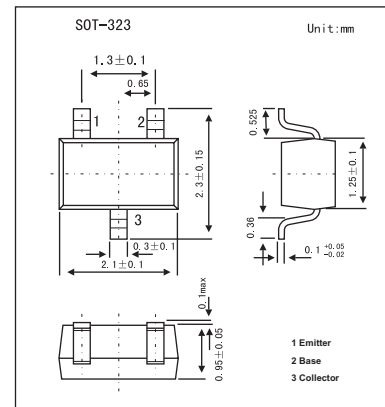


## Silicon PNP Epitaxial Planar Type

## 2SA1532

## ■ Features

- High transition frequency fr.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-30	V
Collector-emitter voltage	V <sub>CEO</sub>	-20	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-30	mA
Collector power dissipation	P <sub>C</sub>	150	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Base-emitter saturation voltage	V <sub>BE</sub>	V <sub>CE</sub> = -10 V, I <sub>C</sub> = -1 mA		-0.7		V
Collector-base cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0			-0.1	μA
Collector-emitter cutoff current	I <sub>CEO</sub>	V <sub>CE</sub> = -20 V, I <sub>B</sub> = 0			-100	μA
Emitter-base cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = -5 V, I <sub>C</sub> = 0			-10	μA
Forward current transfer ratio	h <sub>FE</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 1 mA	50		220	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> = -1 mA		-0.1		V
Transition frequency	f <sub>T</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 1 mA, f = 200 MHz	150	300		MHz
Noise voltage	NF	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 1 mA, f = 5 MHz		2.8	4.0	dB
Reverse transfer impedance	Z <sub>rb</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 1 mA, f = 2 MHz		22	60	Ω
Common-emitter reverse transfer capacitance	C <sub>re</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 1 mA, f = 10.7 MHz		1.2	2.0	pF

## ■ hFE Classification

Marking	E		
	A	B	C
hFE	50~100	70~140	110~220